

Surface Engineered Iron Oxide Nanoparticles Prepared by Inert Gas Condensation for Biomedical Applications

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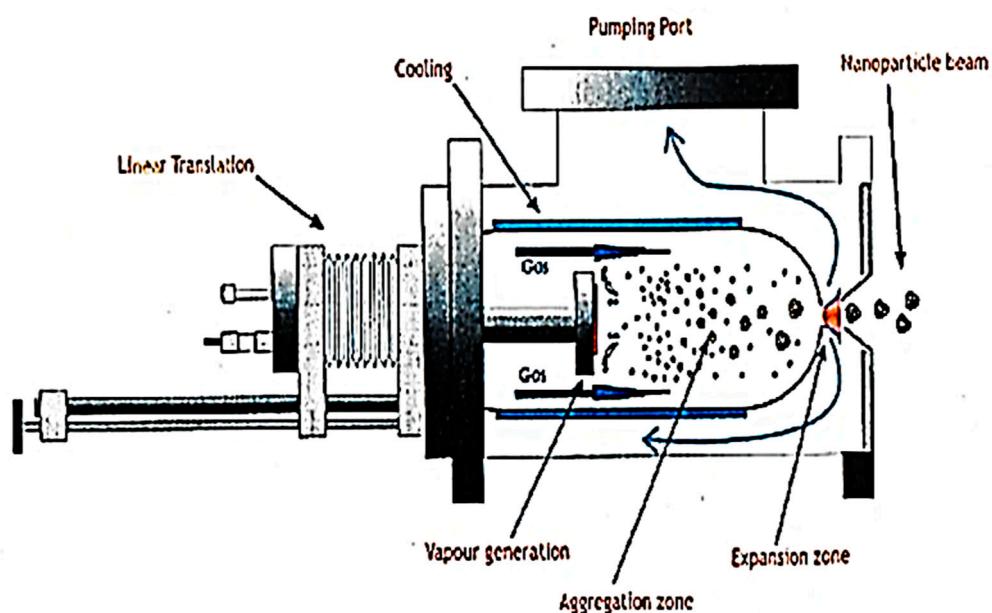
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Supporting Information

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Scheme S1



Scheme S1: Production of IONPs by inert gas condensation [33]

Figure S1.

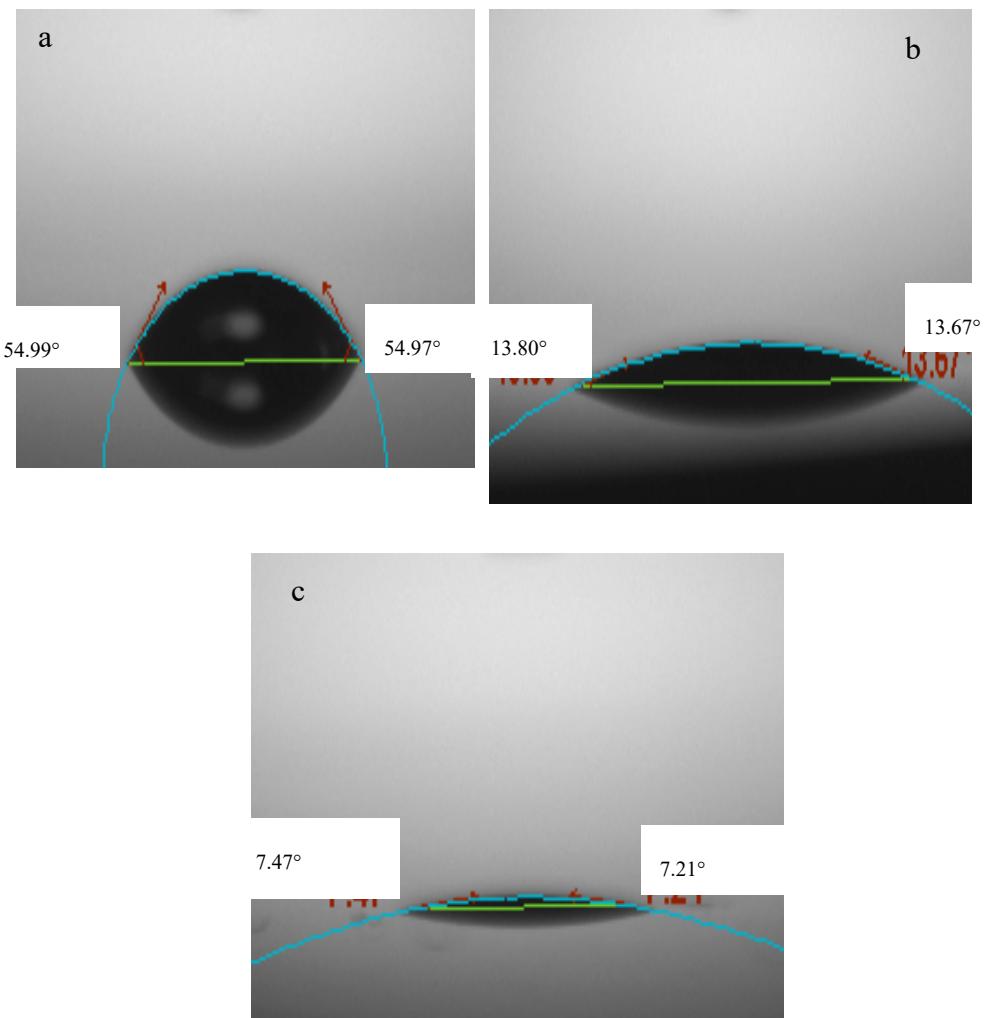
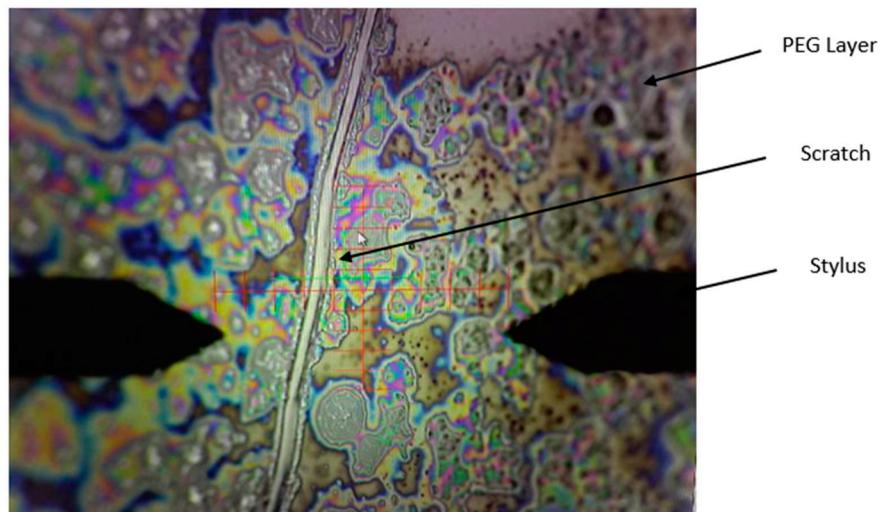


Figure S1: Contact angle measurement bare silicon wafer (a) PEG-coated wafer (b) IONPs deposited on PEG coated wafer (c).

Figure S2.



Figures S2. Scratched PEG-coated silicon wafer

Table S1

Table S1: Conditions tested to produce IONPs using the Mantis NanoGene Trio system.

| Main chamber pressure (Torr) | Temperature (°c) | WD (cm) | Throttle position (%) |
|---------------------------------|---------------------|------------|--------------------------|
| $2.84 \cdot 10^{-5}$ | 17 | 13.8 | 0 |
| $7.36 \cdot 10^{-4}$ | 16 | 13.8 | 50 |
| $1.32 \cdot 10^{-3}$ | 16 | 13.8 | 70 |

Table S2

Table S2: Mantis NanoGene Trio system parameters adjustment to achieve and maintain a plasma.

| t ₀ minutes | | t ₃₀ minutes | | t ₆₀ minutes | | t ₉₀ minutes | | t ₁₂₀ minutes | |
|------------------------|-------------|-------------------------|-------------|-------------------------|-------------|-------------------------|-------------|--------------------------|-------------|
| Volts (V) | Amps (A) | Volts (V) | Amps (A) | Volts (V) | Amps (A) | Volts (V) | Amps (A) | Volts (V) | Amps (A) |
| 454.0 | 0.110 | 455.0 | 0.110 | 456.0 | 0.109 | 438.0 | 0.109 | 458.0 | 0.103 |
| 459.7 | 0.109 | 404.5 | 0.108 | 456.0 | 0.107 | 468.0 | 0.107 | 468.0 | 0.107 |
| 460.0 | 0.109 | 465.4 | 0.106 | 467.0 | 0.106 | 461.1 | 0.107 | 463.0 | 0.109 |
| 468.0 | 0.107 | 466.5 | 0.107 | 468.0 | 0.107 | 467.0 | 0.101 | 466 | 0.107 |
| 458.5 | 0.114 | 472.1 | 0.114 | 488.0 | 0.110 | 488.0 | 0.100 | 487.0 | 0.110 |
| 492.1 | 0.100 | 490.0 | 0.100 | 492.3 | 0.100 | 491.2 | 0.100 | 493.5 | 0.100 |
| 531.9 | 0.038 | 531.6 | 0.030 | 529.0 | 0.030 | 528.3 | 0.030 | 524.2 | 0.031 |

Table S3

Table S3: Changes on the flow rate of argon in relation to the power and throttle position.

| Throttle position (%) | WD (cm) | Argon flow (sccm) | Average power (Watts) |
|-----------------------|---------|-------------------|-----------------------|
| 50 | 13.8 | 30 | 49.95 |
| 70 | 13.8 | 70 | 49.2 |
| 80 | 13.8 | 100 | 41.2 |